

EAST Search History

| Ref # | Hits | Search Query                                  | DBs   | Default Operator | Plurals | Time Stamp          |
|-------|------|---|---|------------------|---------|---------------------|
|       |      | S24 near10 (thermal or heating)               | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2009/04/13<br>09:15 |
|       |      | S4 and (dose same nitride                     | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2009/04/07<br>10:34 |
| L1    | 0    | silicon oxynitride near nitiding near plasma  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2009/04/13<br>10:55 |
| L2    | 0    | silicon oxynitride near nitriding near plasma | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2009/04/13<br>10:55 |
| L3    | 0    | silicon oxynitride near nitriding andplasma   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ              | ON      | 2009/04/13<br>10:55 |

|    |    |   |   |     |    |                     |
|----|----|---|---|-----|----|---------------------|
| L4 | 7  | silicon oxynitride near nitriding and plasma  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>10:55 |
| L5 | 68 | silicon oxynitride same nitriding near plasma | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>10:55 |
| L6 | 13 | I5 and wet etching                            | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>11:21 |
| L7 | 0  | I5 and wet etch                               | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>11:24 |
| L8 | 20 | I5 and wet                                    | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>11:24 |
| L9 | 87 | silicon oxide and (trench near wet etch\$3)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>11:25 |

|     |     |   |   |     |    |                     |
|-----|-----|---|---|-----|----|---------------------|
| S1  | 749 | (rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and (nitrogen or nitride or nitrification) | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/07<br>09:42 |
| S2  | 577 | S1 and pressure   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/07<br>09:42 |
| S3  | 10  | S2 and lower pressure   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/07<br>09:42 |
| S4  | 74  | S2 and reduced pressure   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/07<br>09:42 |
| S8  | 18  | S4 and dose   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/07<br>10:32 |
| S10 | 2   | S4 and (dose same nitride)  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/07<br>10:34 |

|     |      |   |  |     |    |                     |
|-----|------|---|--|-----|----|---------------------|
| S11 | 23   | S4 and (dose or concentration same nitride)   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>10:34 |
| S13 | 3    | S4 and ppm  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>10:37 |
| S14 | 211  | (rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and (nitrogen or nitride or nitrification) and (dose or ppm)     | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>10:38 |
| S15 | 14   | (rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and ((nitrogen or nitride or nitrification) near5 (dose or ppm)) | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>10:39 |
| S16 | 0    | 438/197,261,287,591,770,773,775,787,788,792   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>16:26 |
| S17 | 8589 | 438/197,261,287,591,770,773,775,787,788,792.ccls.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>16:26 |

|     |      |   |  |     |    |                     |
|-----|------|---|--|-----|----|---------------------|
| S18 | 749  | (rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and (nitrogen or nitride or nitrification) | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>16:26 |
| S19 | 109  | S17 and S18   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>16:26 |
| S20 | 13   | S19 and reduced pressure  | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/07<br>16:26 |
| S21 | 101  | "5,939,763"   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/13<br>09:07 |
| S22 | 2    | "5,939,763".pn.   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/13<br>09:07 |
| S23 | 9388 | thin\$4 near (silicon oxide or "SiO.sub.2")   | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>BM_TDB | ADJ | ON | 2009/04/13<br>09:10 |

|     |      |  |   |     |    |                     |
|-----|------|--|---|-----|----|---------------------|
| S24 | 7477 | S23 and (thermal or heat\$3)                 | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:10 |
| S25 | 564  | S24 and thinning                             | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:11 |
| S26 | 95   | thinning near (silicon oxide or "SiO.sub.2") | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:11 |
| S27 | 77   | S26 and (thermal or heating\$3)              | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:11 |
| S28 | 1    | S26 near (thermal or heating\$3)             | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:14 |
| S29 | 0    | ("2008/0096395").URPN.                       | USPAT   | ADJ | ON | 2009/04/13<br>09:15 |
| S30 | 0    | ("2008/0096395").URPN.                       | USPAT   | ADJ | ON | 2009/04/13<br>09:15 |

|     |     |                                 |   |     |    |                     |
|-----|-----|---------------------------------|---|-----|----|---------------------|
| S31 | 692 | S23 near10 (thermal or heating) | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:15 |
| S32 | 356 | "I19" and annealing             | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:16 |
| S33 | 322 | "I16" and annealing             | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:16 |
| S34 | 271 | S31 and annealing               | US-PGPUB;<br>USPAT;<br>USOCR; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | ADJ | ON | 2009/04/13<br>09:16 |

4/ 13/ 2009 11:38:54 AM  
C:\ Documents and Settings\ jhan4\ My Documents\ EAST\ Workspaces\ 10594739.wsp